ESD Protection Diode

Micro-Packaged Diodes for ESD Protection

ESDL2012

The ESDL2012 is designed to protect voltage sensitive components that require low capacitance from ESD and transient voltage events. Excellent clamping capability, low capacitance, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its low capacitance, the part is well suited for use in high speed data line applications.

Features

- Low Capacitance
- Low Clamping Voltage
- Small Body Outline Dimensions: 0.60 mm x 0.30 mm
- Low Body Height: 0.2 mm
- Stand-off Voltage: 1.0 V
- IEC61000-4-2 Level 4 ESD Protection
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- SZESDL2012MX2WT5G Wettable Flank Package for optimal Automated Optical Inspection (AOI)
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- USB 3.x
- Thunderbolt 3.0

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
IEC 61000-4-2 (ESD) Contact Air		±16 ±16	kV
Total Power Dissipation on FR-4 Board (Note 1) @ T _A = 25°C Thermal Resistance, Junction-to-Ambient	P_{D} $R_{ hetaJA}$	313 400	mW °C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C
Lead Solder Temperature – Maximum (10 Second Duration)	TL	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-4 = 28 mm² 1 oz. Cu JEDEC JESD51-3 two layer PCB.

ON

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DIAGRAM

OFN2

X4DFN2 (0201) CASE 152AX



MARKING

K = Specific Device CodeM = Date Code



AAN

X2DFNW2 CASE 717AB

AA = Specific Device Code

M = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
ESDL2012MX4T5G	X4DFN2 (Pb-Free)	10000 / Tape & Reel
SZESDL2012MX2WT5G	X2DFNW2 (Pb-Free)	8000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

See Application Note AND8308/D for further description of survivability specs.

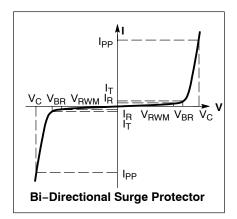
1

ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Symbol	Parameter		
I _{PP}	Maximum Reverse Peak Pulse Current		
V _C	Clamping Voltage @ I _{PP}		
V _{RWM}	Working Peak Reverse Voltage		
I _R	Maximum Reverse Leakage Current @ V _{RWM}		
V _{BR}	Breakdown Voltage @ I _T		
I _T	Test Current		

^{*}See Application Note AND8308/D for detailed explanations of datasheet parameters.



ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

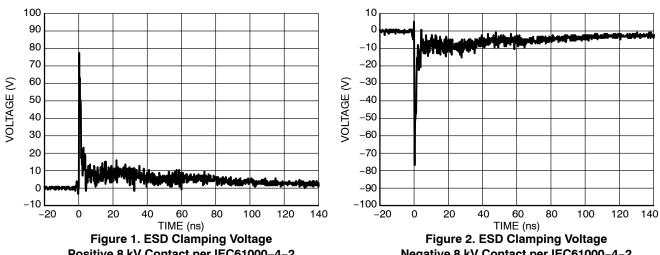
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Reverse Working Voltage	V_{RWM}	I/O Pin to GND			1.0	٧
Breakdown Voltage	V_{BR}	I _T = 1 mA, I/O Pin to GND		1.6	2.1	V
Reverse Leakage Current	I _R	V _{RWM} = 1.0 V		30	500	nA
Clamping Voltage (Note 2)	V _C	IEC61000-4-2, ±8 kV Contact		Figures 1 and 2		V
Clamping Voltage, 200 ns TLP,	V _C	Ipp = 4 A		3.5	4.0	V
IEC61000-4-2 Level 1 Equivalent (±2 kV Contact, ±4 kV Air)		I _{PP} = 4 A (SZESDL2012)			5.0	
IEC61000-4-2 Level 2 Equivalent		I _{PP} = 8 A		4.7	5.2	
(±4 kV Contact, ±8 kV Air)		I _{PP} = 8 A (SZESDL2012)			7.5	
Reverse Peak Pulse Current per Figure 12	l _{PP}	per IEC61000-4-5 (1.2/50 μ s), R _{eq} = 12 Ω	3.5	4.7		Α
Clamping Voltage,	V _C	I_{PP} = 2.1 A, R_{eq} = 12 Ω		3.1	3.4	V
IEC61000-4-5 (1.2/50 μs) Waveform per Figure 12		I_{PP} = 2.1 A, R_{eq} = 12 Ω (SZESDL2012)			4.5	
Clamping Voltage,	V _C	I_{PP} = 3.5 A, R_{eq} = 12 Ω		3.7	4.1	V
IEC61000-4-5 (1.2/50 μs) Waveform per Figure 12		I_{PP} = 3.5 A, R_{eq} = 12 Ω (SZESDL2012)			5.5	
Dynamic Resistance (200 ns TLP, 4 A to 8 A)	R _{DYN}	I/O Pin to GND I/O Pin to GND (SZESDL2012)		0.30 0.65		Ω
Junction Capacitance	CJ	$V_R = 0 \text{ V, f} = 1 \text{ MHz}$ $V_R = 0 \text{ V, f} = 1 \text{ MHz}$ (SZESDL2012)		0.18 0.25	0.23 0.35	pF
Insertion Loss (ESDL2012MX4 only)	ΙL	f = 10 GHz f = 13 GHz		0.26 0.27	0.33 0.36	dB
		f = 15 GHz		0.28	0.37	
Return Loss (ESDL2012MX4 only)	R_{L}	f = 10 GHz f = 13 GHz f = 15 GHz	14 12 11	16 14 13		dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{2.} For test procedure see application note AND8307/D.

^{3.} ANSI/ESD STM5.5.1 – Electrostatic Discharge Sensitivity Testing using Transmission Line Pulse (TLP) Model. TLP conditions: $Z_0 = 50 \Omega$, $t_p = 200 \text{ ns}$, $t_r = 1 \text{ ns}$, averaging window; $t_1 = 170 \text{ ns}$ to $t_2 = 190 \text{ ns}$.

TYPICAL CHARACTERISTICS



Positive 8 kV Contact per IEC61000-4-2

Negative 8 kV Contact per IEC61000-4-2

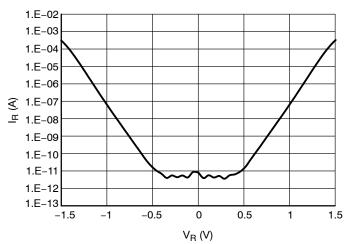


Figure 3. IV Characteristics

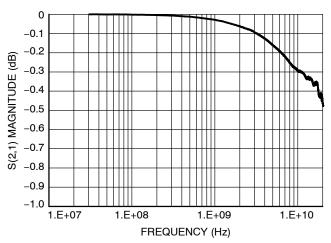


Figure 4. Insertion Loss

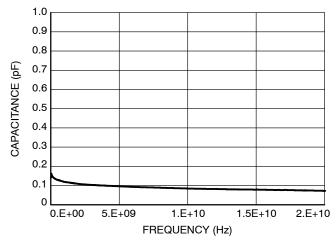


Figure 5. Capacitance Over Frequency

TYPICAL CHARACTERISTICS

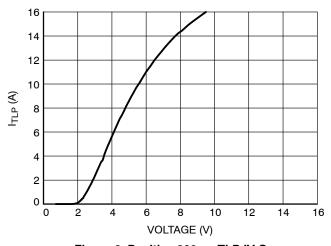


Figure 6. Positive 200 ns TLP IV Curve

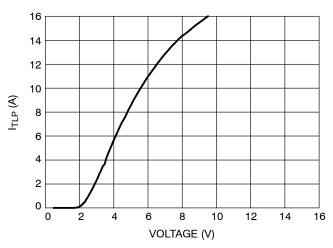


Figure 7. Negative 200 ns TLP IV Curve

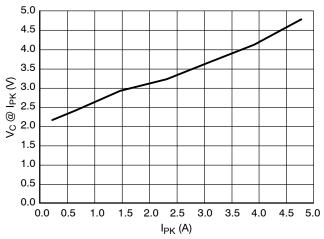


Figure 8. Positive Clamping Voltage vs. Peak Pulse Current (per IEC61000–4–5 (tp = 1.2/50 $\mu s,\,R_{eq}$ = 12 $\Omega))$

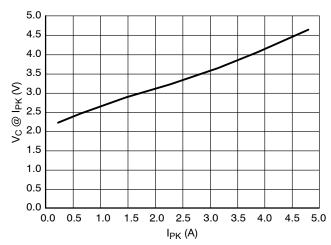


Figure 9. Negative Clamping Voltage vs. Peak Pulse Current (per IEC61000–4–5 (tp = 1.2/50 $\mu s,\,R_{eq}$ = 12 $\Omega))$

IEC 61000-4-2 Spec.

Level	Test Volt- age (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8

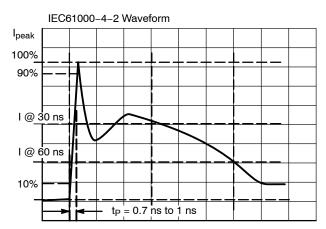


Figure 10. IEC61000-4-2 Spec

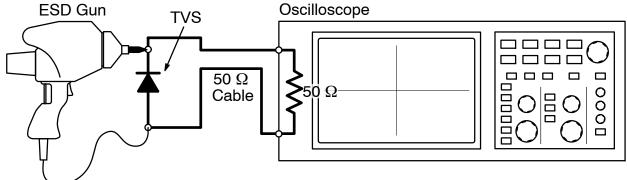


Figure 11. Diagram of ESD Test Setup

ESD Voltage Clamping

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000-4-2 waveform. Since the IEC61000-4-2 was written as a pass/fail spec for larger systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage

at the device level. ON Semiconductor has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how ON Semiconductor creates these screenshots and how to interpret them please refer to AND8307/D.

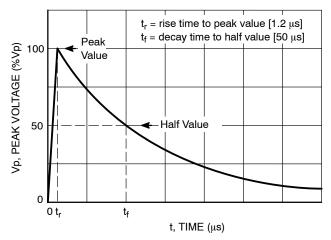
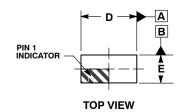
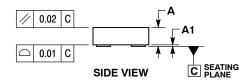


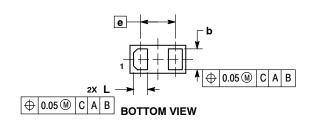
Figure 12. IEC61000-4-5 1.2/50 μs Pulse Waveform

PACKAGE DIMENSIONS

DFN2, 0.60x0.30, 0.36P CASE 152AX ISSUE G



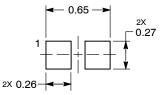




- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.

	MILLIMETERS			
DIM	MIN	NOM	MAX	
Α	0.175	0.200	0.225	
A1	0.018 REF			
b	0.205	0.215	0.225	
D	0.575	0.600	0.625	
Е	0.275	0.300	0.325	
е	0.36 BSC			
L	0.145	0.155	0.165	

RECOMMENDED SOLDER FOOTPRINT*



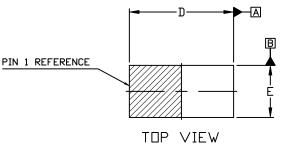
DIMENSIONS: MILLIMETERS

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

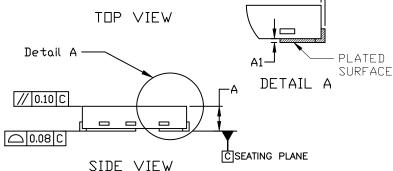
X2DFNW2 1.60x0.80

CASE 717AB **ISSUE B**

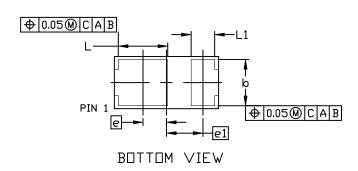


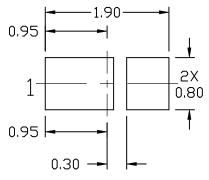


- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS



	MILLIMETERS			
DIM	MIN.	N□M.	MAX.	
Α	0.34	0.37	0.40	
A1			0.04	
b	0.67	0.71	0.75	
D	1.55	1.60	1.65	
D1			0.04	
Ε	0.75	0.80	0.85	
е	0.36 BSC			
e1	0.56 BSC			
L	0.72	0.76	0.80	
L1	0.32	0.36	0.40	





RECOMMENDED MOUNTING FOOTPRINT*

For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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